

# STARPOWER

## SEMICONDUCTOR

## IGBT

# GD15PJX120L2S

**1200V/15A PIM in one-package**

## General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness.

They are designed for the applications such as general inverters and UPS.

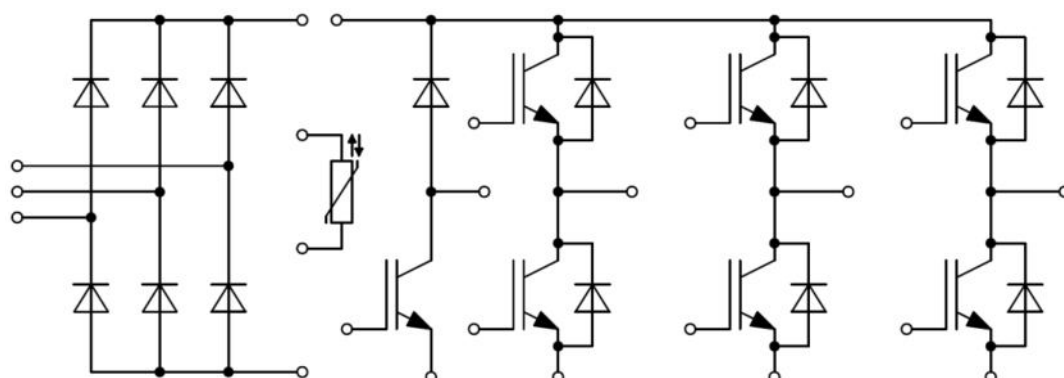
## Features

- Low  $V_{CE(sat)}$  Trench IGBT technology
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

## Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

## Equivalent Circuit Schematic



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT-inverter**

| Symbol    | Description                                           | Value    | Unit |
|-----------|-------------------------------------------------------|----------|------|
| $V_{CES}$ | Collector-Emitter Voltage                             | 1200     | V    |
| $V_{GES}$ | Gate-Emitter Voltage                                  | $\pm 20$ | V    |
| $I_C$     | Collector Current @ $T_C=25^{\circ}\text{C}$          | 30       | A    |
|           | @ $T_C=100^{\circ}\text{C}$                           | 15       |      |
| $I_{CM}$  | Pulsed Collector Current $t_p=1\text{ms}$             | 30       | A    |
| $P_D$     | Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$ | 173      | W    |

**Diode-inverter**

| Symbol    | Description                                    | Value | Unit |
|-----------|------------------------------------------------|-------|------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage                | 1200  | V    |
| $I_F$     | Diode Continuous Forward Current               | 15    | A    |
| $I_{FM}$  | Diode Maximum Forward Current $t_p=1\text{ms}$ | 30    | A    |

**Diode-rectifier**

| Symbol    | Description                                                        | Value | Unit                 |
|-----------|--------------------------------------------------------------------|-------|----------------------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage                                    | 1600  | V                    |
| $I_O$     | Average Output Current 50Hz/60Hz,sine wave                         | 15    | A                    |
| $I_{FSM}$ | Surge Forward Current $t_p=10\text{ms}$ @ $T_j=25^{\circ}\text{C}$ | 300   | A                    |
|           | @ $T_j=150^{\circ}\text{C}$                                        | 245   |                      |
| $I^2t$    | $I^2t$ -value, $t_p=10\text{ms}$ @ $T_j=25^{\circ}\text{C}$        | 450   | $\text{A}^2\text{s}$ |
|           | @ $T_j=150^{\circ}\text{C}$                                        | 300   |                      |

**IGBT-brake**

| Symbol    | Description                                           | Value    | Unit |
|-----------|-------------------------------------------------------|----------|------|
| $V_{CES}$ | Collector-Emitter Voltage                             | 1200     | V    |
| $V_{GES}$ | Gate-Emitter Voltage                                  | $\pm 20$ | V    |
| $I_C$     | Collector Current @ $T_C=25^{\circ}\text{C}$          | 30       | A    |
|           | @ $T_C=100^{\circ}\text{C}$                           | 15       |      |
| $I_{CM}$  | Pulsed Collector Current $t_p=1\text{ms}$             | 30       | A    |
| $P_D$     | Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$ | 178      | W    |

**Diode-brake**

| Symbol    | Description                                    | Value | Unit |
|-----------|------------------------------------------------|-------|------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage                | 1200  | V    |
| $I_F$     | Diode Continuous Forward Current               | 10    | A    |
| $I_{FM}$  | Diode Maximum Forward Current $t_p=1\text{ms}$ | 20    | A    |

**Module**

| Symbol     | Description                                              | Value       | Unit               |
|------------|----------------------------------------------------------|-------------|--------------------|
| $T_{jmax}$ | Maximum Junction Temperature(inverter,brake)             | 175         | $^{\circ}\text{C}$ |
|            | Maximum Junction Temperature (rectifier)                 | 150         |                    |
| $T_{jop}$  | Operating Junction Temperature                           | -40 to +150 | $^{\circ}\text{C}$ |
| $T_{STG}$  | Storage Temperature Range                                | -40 to +125 | $^{\circ}\text{C}$ |
| $V_{ISO}$  | Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$ | 2500        | V                  |

**IGBT-inverter Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

| Symbol        | Parameter                               | Test Conditions                                                                                                   | Min. | Typ. | Max. | Unit          |
|---------------|-----------------------------------------|-------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_{CE(sat)}$ | Collector to Emitter Saturation Voltage | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$                                                         |      | 1.75 | 2.20 | V             |
|               |                                         | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$                                                        |      | 2.00 |      |               |
|               |                                         | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$                                                        |      | 2.05 |      |               |
| $V_{GE(th)}$  | Gate-Emitter Threshold Voltage          | $I_C=0.60\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$                                                          | 5.6  | 6.2  | 6.8  | V             |
| $I_{CES}$     | Collector Cut-Off Current               | $V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$                                                          |      |      | 1.0  | mA            |
| $I_{GES}$     | Gate-Emitter Leakage Current            | $V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$                                                          |      |      | 400  | nA            |
| $R_{Gint}$    | Internal Gate Resistance                |                                                                                                                   |      | 0    |      | $\Omega$      |
| $C_{ies}$     | Input Capacitance                       | $V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$                                                              |      | 1.55 |      | nF            |
| $C_{res}$     | Reverse Transfer Capacitance            |                                                                                                                   |      | 0.04 |      | nF            |
| $Q_G$         | Gate Charge                             | $V_{GE}=-15\dots+15\text{V}$                                                                                      |      | 0.12 |      | $\mu\text{C}$ |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$                   |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                   |      | 50   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                   |      | 191  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                   |      | 142  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                   |      | 1.11 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                   |      | 0.81 |      | mJ            |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$                  |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                   |      | 56   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                   |      | 269  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                   |      | 186  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                   |      | 1.50 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                   |      | 1.18 |      | mJ            |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$                  |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                   |      | 56   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                   |      | 274  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                   |      | 210  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                   |      | 1.67 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                   |      | 1.32 |      | mJ            |
| $I_{SC}$      | SC Data                                 | $t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$ |      | 60   |      | A             |

**Diode-inverter Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol    | Parameter                     | Test Conditions                                                                                                         | Min. | Typ. | Max. | Unit          |
|-----------|-------------------------------|-------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_F$     | Diode Forward Voltage         | $I_F=15\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                              |      | 1.85 | 2.30 | V             |
|           |                               | $I_F=15\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$                                                             |      | 1.90 |      |               |
|           |                               | $I_F=15\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$                                                             |      | 1.95 |      |               |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=15\text{A},$<br>$-di/dt=540\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=25^{\circ}\text{C}$  |      | 1.4  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 15   |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.36 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=15\text{A},$<br>$-di/dt=540\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=125^{\circ}\text{C}$ |      | 2.4  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 14   |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.67 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=15\text{A},$<br>$-di/dt=540\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=150^{\circ}\text{C}$ |      | 2.8  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 14   |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.78 |      | mJ            |

**Diode-rectifier Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol | Parameter             | Test Conditions                             | Min. | Typ. | Max. | Unit |
|--------|-----------------------|---------------------------------------------|------|------|------|------|
| $V_F$  | Diode Forward Voltage | $I_F=15\text{A}, T_j=150^{\circ}\text{C}$   |      | 0.85 |      | V    |
| $I_R$  | Reverse Current       | $T_j=150^{\circ}\text{C}, V_R=1600\text{V}$ |      |      | 3.0  | mA   |

**IGBT-brake Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol        | Parameter                               | Test Conditions                                                                                                     | Min. | Typ. | Max. | Unit          |
|---------------|-----------------------------------------|---------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_{CE(sat)}$ | Collector to Emitter Saturation Voltage | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$                                                         |      | 1.75 | 2.20 | V             |
|               |                                         | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$                                                        |      | 2.00 |      |               |
|               |                                         | $I_C=15\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$                                                        |      | 2.05 |      |               |
| $V_{GE(th)}$  | Gate-Emitter Threshold Voltage          | $I_C=0.60\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$                                                          | 5.6  | 6.2  | 6.8  | V             |
| $I_{CES}$     | Collector Cut-Off Current               | $V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                          |      |      | 1.0  | mA            |
| $I_{GES}$     | Gate-Emitter Leakage Current            | $V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                          |      |      | 400  | nA            |
| $R_{Gint}$    | Internal Gate Resistance                |                                                                                                                     |      | 0    |      | $\Omega$      |
| $C_{ies}$     | Input Capacitance                       | $V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$                                                                |      | 1.55 |      | nF            |
| $C_{res}$     | Reverse Transfer Capacitance            |                                                                                                                     |      | 0.04 |      | nF            |
| $Q_G$         | Gate Charge                             | $V_{GE}=-15\dots+15\text{V}$                                                                                        |      | 0.12 |      | $\mu\text{C}$ |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$                   |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 50   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 191  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 142  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 1.11 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 0.81 |      | mJ            |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$                  |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 56   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 269  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 186  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 1.50 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 1.18 |      | mJ            |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=15\text{A}, R_G=39\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$                  |      | 47   |      | ns            |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 56   |      | ns            |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 274  |      | ns            |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 210  |      | ns            |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 1.67 |      | mJ            |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 1.32 |      | mJ            |
| $I_{SC}$      | SC Data                                 | $t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$ |      | 60   |      | A             |

**Diode-brake Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol    | Parameter                     | Test Conditions                                                                                                         | Min. | Typ. | Max. | Unit          |
|-----------|-------------------------------|-------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_F$     | Diode Forward Voltage         | $I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                              |      | 1.85 | 2.30 | V             |
|           |                               | $I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$                                                             |      | 1.90 |      |               |
|           |                               | $I_F=10\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$                                                             |      | 1.95 |      |               |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=10\text{A},$<br>$-di/dt=490\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=25^{\circ}\text{C}$  |      | 1.0  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 14   |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.24 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=10\text{A},$<br>$-di/dt=490\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=125^{\circ}\text{C}$ |      | 2.0  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 12   |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.51 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=10\text{A},$<br>$-di/dt=490\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=150^{\circ}\text{C}$ |      | 2.2  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                         |      | 9    |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                         |      | 0.58 |      | mJ            |

**NTC Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol       | Parameter              | Test Conditions                                        | Min. | Typ. | Max. | Unit             |
|--------------|------------------------|--------------------------------------------------------|------|------|------|------------------|
| $R_{25}$     | Rated Resistance       |                                                        |      | 5.0  |      | $\text{k}\Omega$ |
| $\Delta R/R$ | Deviation of $R_{100}$ | $T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$         | -5   |      | 5    | %                |
| $P_{25}$     | Power Dissipation      |                                                        |      |      | 20.0 | mW               |
| $B_{25/50}$  | B-value                | $R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$  |      | 3375 |      | K                |
| $B_{25/80}$  | B-value                | $R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$  |      | 3411 |      | K                |
| $B_{25/100}$ | B-value                | $R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$ |      | 3433 |      | K                |

**Module Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol                         | Parameter                                  | Min. | Typ.         | Max.  | Unit       |
|--------------------------------|--------------------------------------------|------|--------------|-------|------------|
| $L_{CE}$                       | Stray Inductance                           |      | 30           |       | nH         |
| $R_{CC'+EE'}$<br>$R_{AA'+CC'}$ | Module Lead Resistance, Terminal to Chip   |      | 8.00<br>6.00 |       | m $\Omega$ |
| $R_{thJC}$                     | Junction-to-Case (per IGBT-inverter)       |      | 0.790        | 0.869 | K/W        |
|                                | Junction-to-Case (per Diode-inverter)      |      | 1.269        | 1.396 |            |
|                                | Junction-to-Case (per Diode-rectifier)     |      | 0.848        | 0.933 |            |
|                                | Junction-to-Case (per IGBT-brake-chopper)  |      | 0.766        | 0.843 |            |
|                                | Junction-to-Case (per Diode-brake-chopper) |      | 1.622        | 1.784 |            |
| $R_{thCH}$                     | Case-to-Heatsink (per IGBT-inverter)       |      | 0.977        |       | K/W        |
|                                | Case-to-Heatsink (per Diode-inverter)      |      | 1.569        |       |            |
|                                | Case-to-Heatsink (per Diode-rectifier)     |      | 1.049        |       |            |
|                                | Case-to-Heatsink (per IGBT-brake-chopper)  |      | 0.948        |       |            |
|                                | Case-to-Heatsink (per Diode-brake-chopper) |      | 2.005        |       |            |
|                                | Case-to-Heatsink (per Module)              |      | 0.058        |       |            |
| F                              | Mounting Force Per Clamp                   | 20   |              | 50    | N          |
| G                              | Weight of Module                           |      | 24           |       | g          |

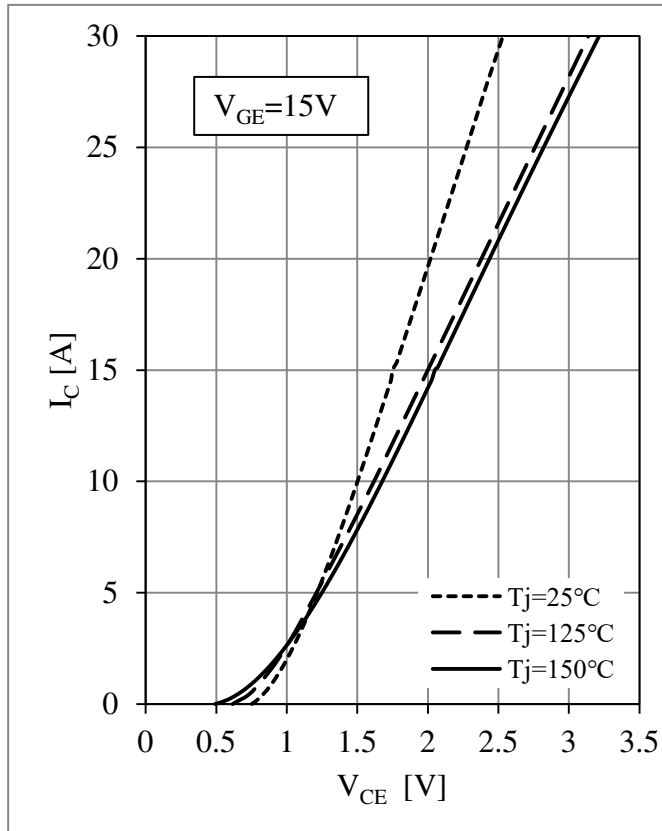


Fig 1. IGBT-inverter Output Characteristics

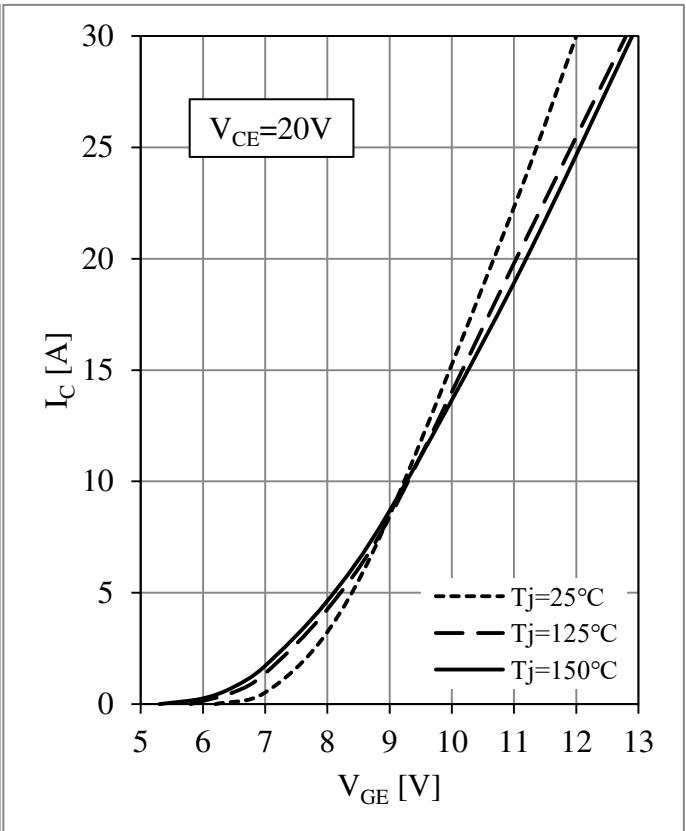
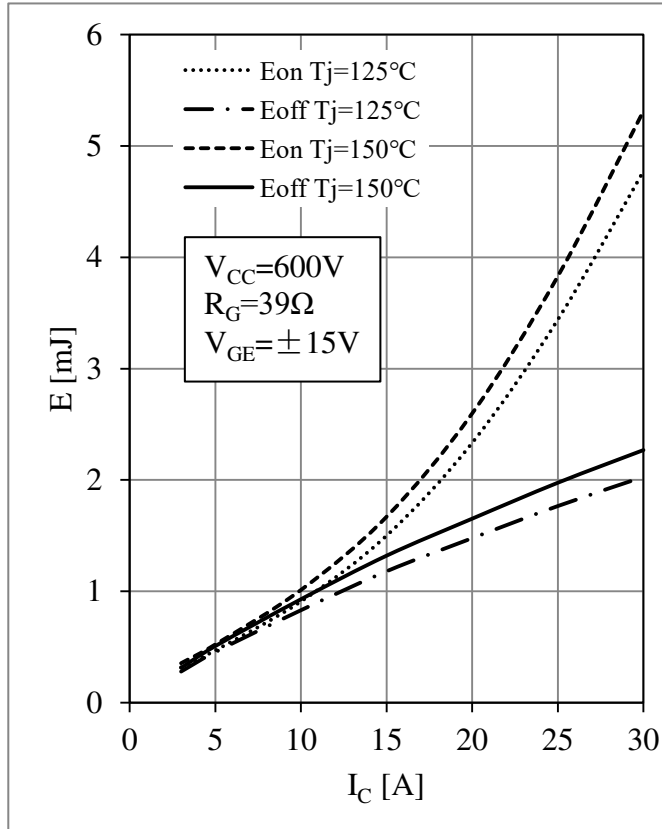
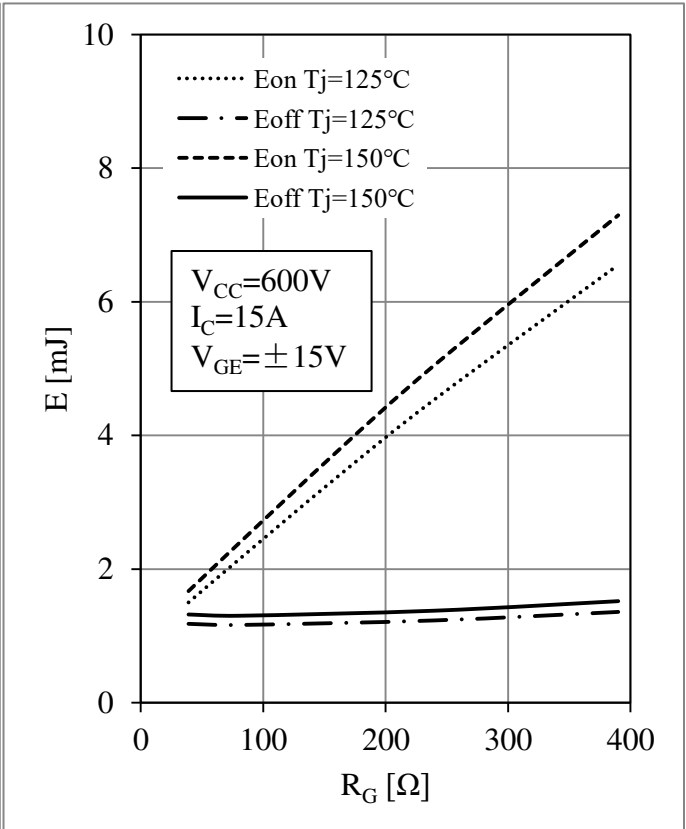


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs.  $I_C$ Fig 4. IGBT-inverter Switching Loss vs.  $R_G$

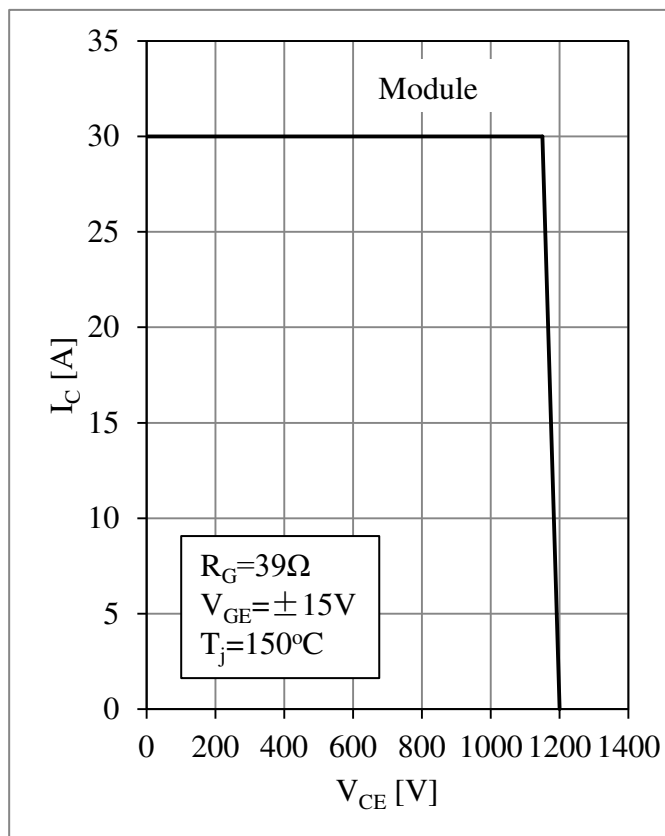


Fig 5. IGBT-inverter RBSOA

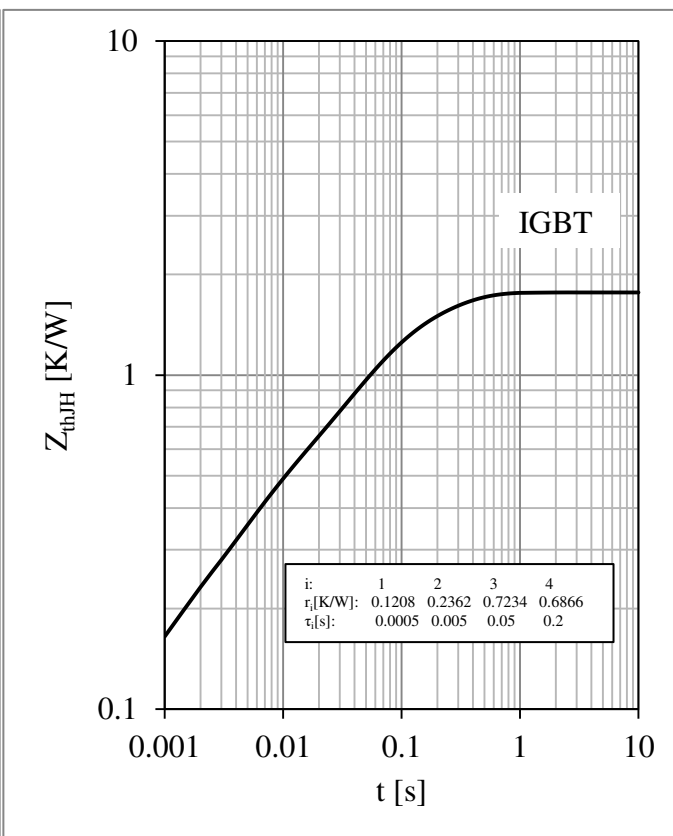


Fig 6. IGBT-inverter Transient Thermal Impedance

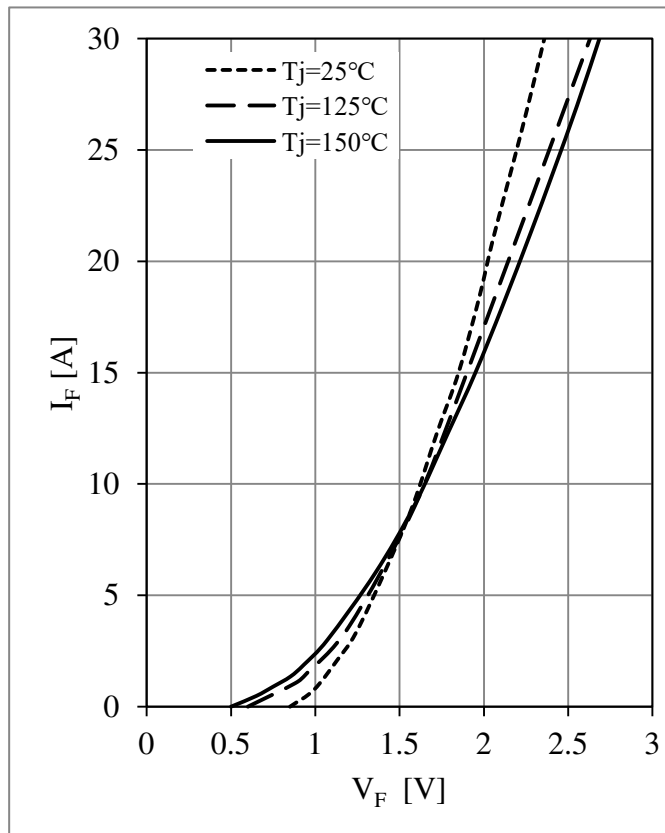
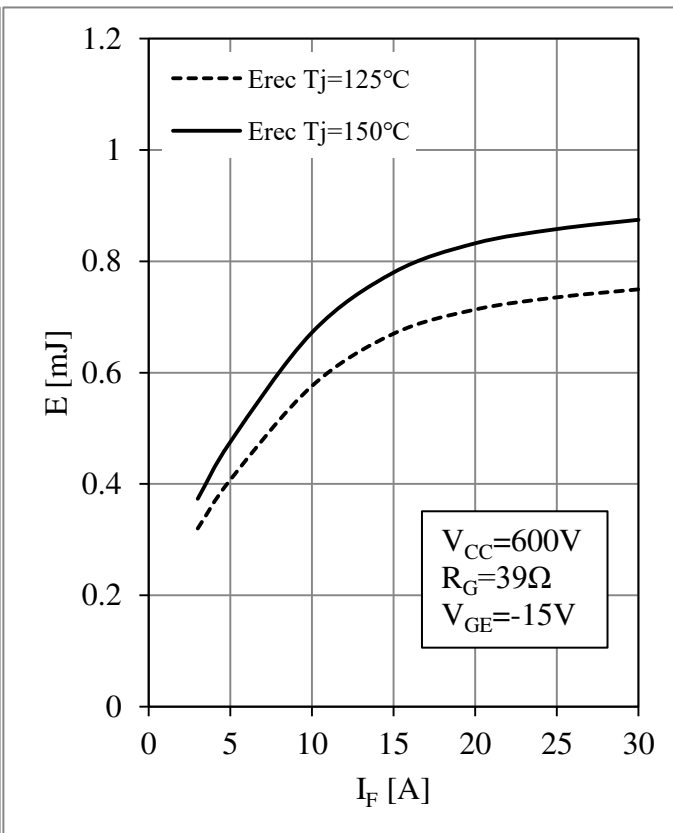
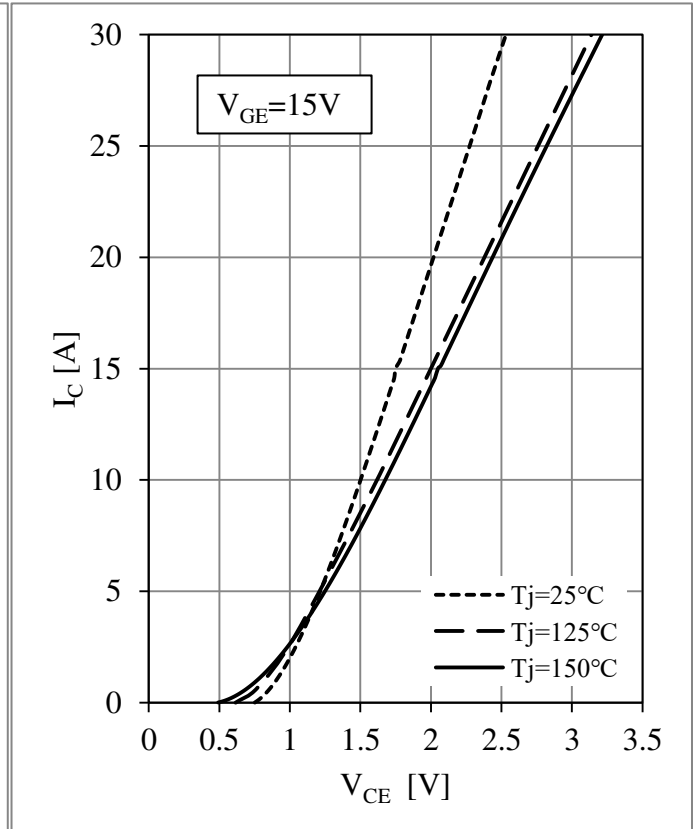
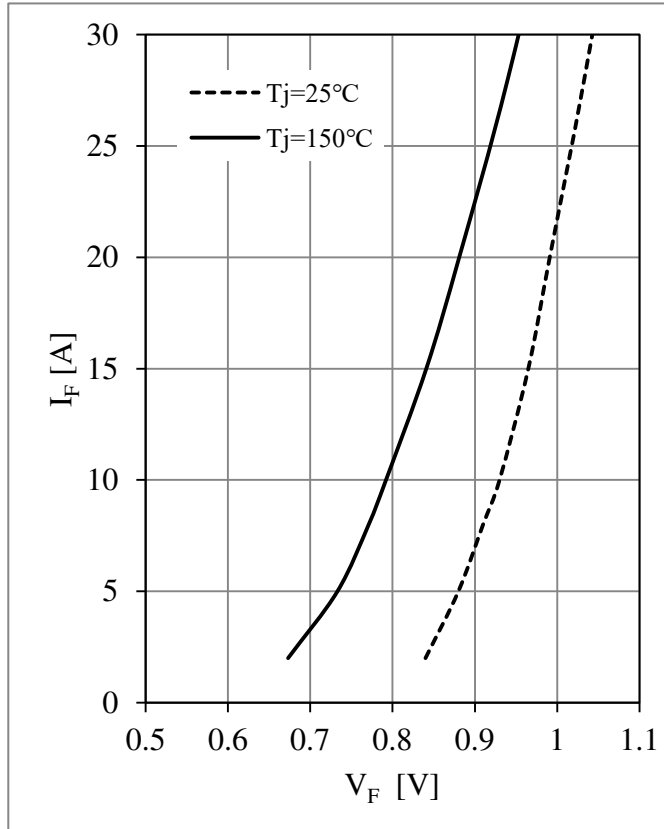
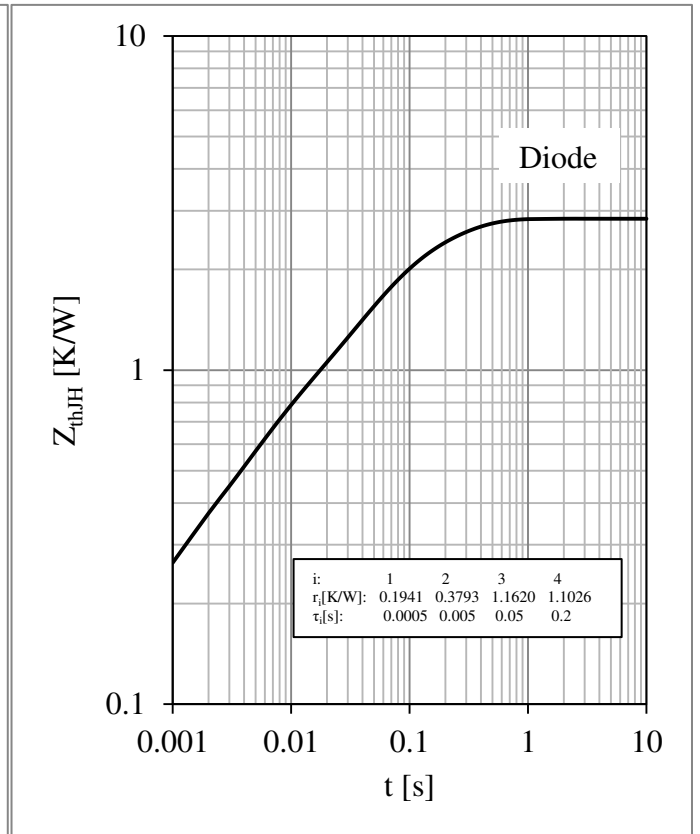
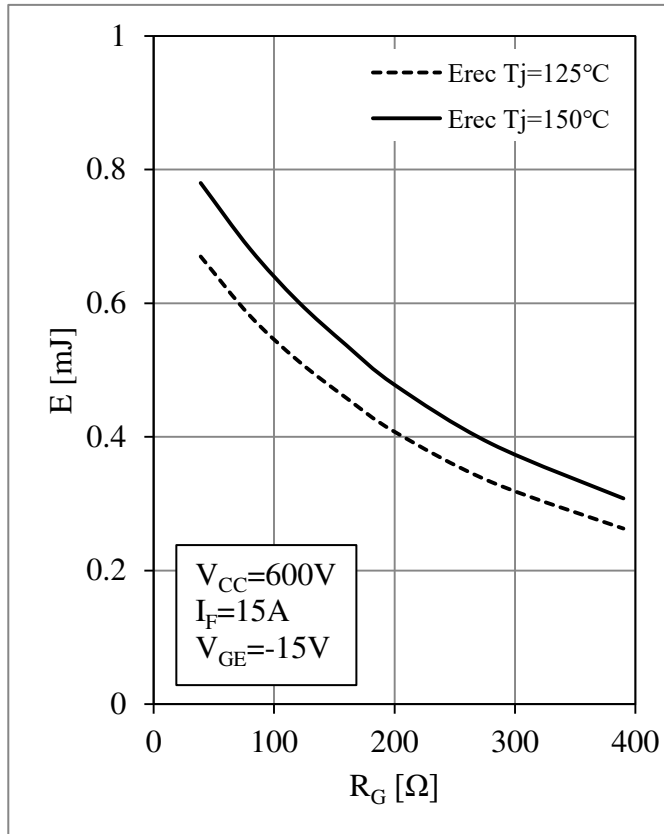


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs.  $I_F$



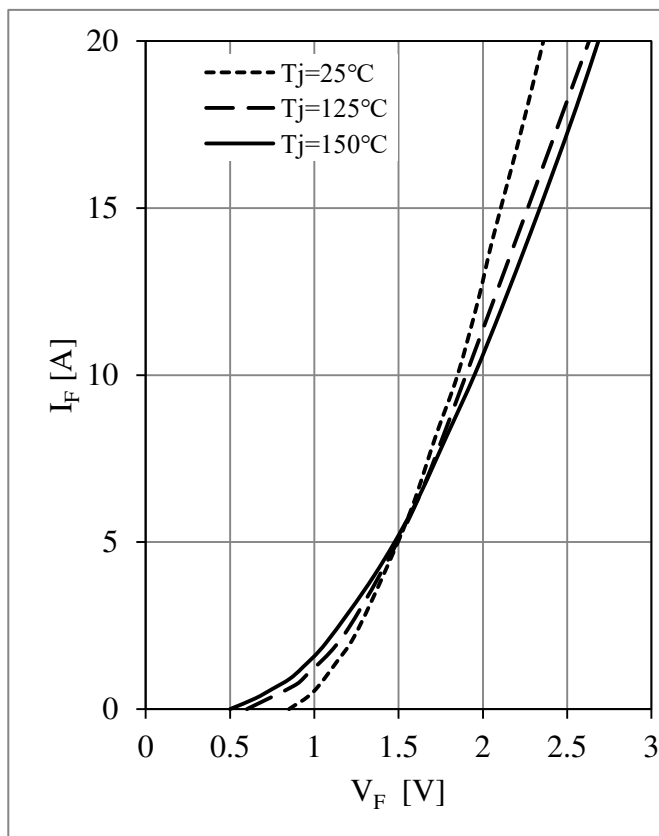


Fig 13. Diode-brake Forward Characteristics

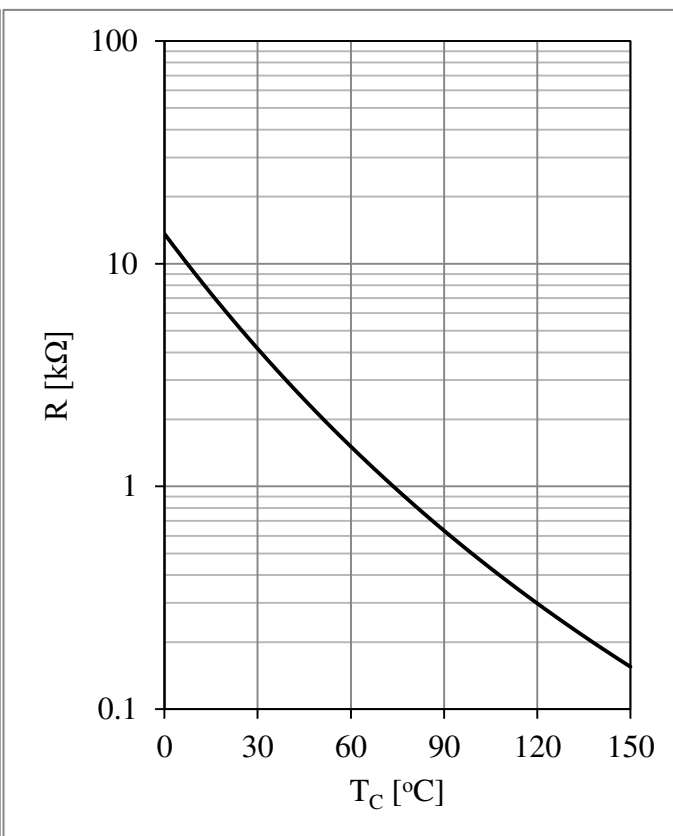
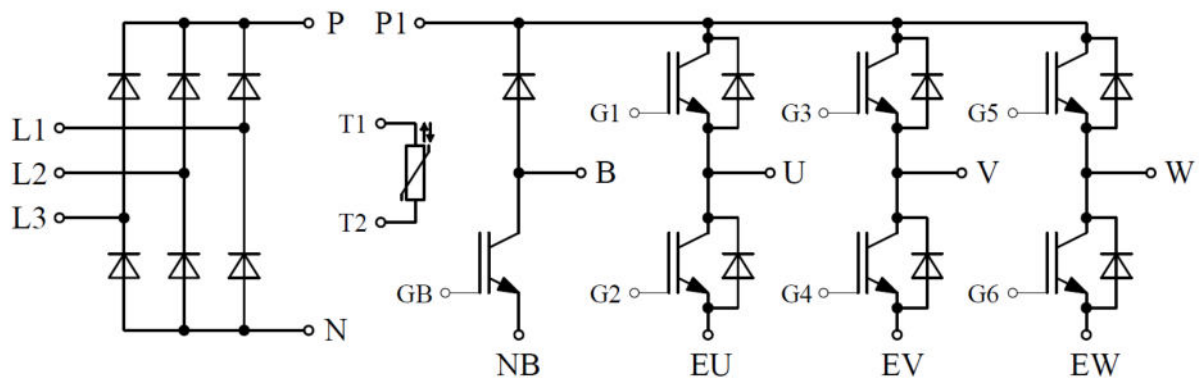


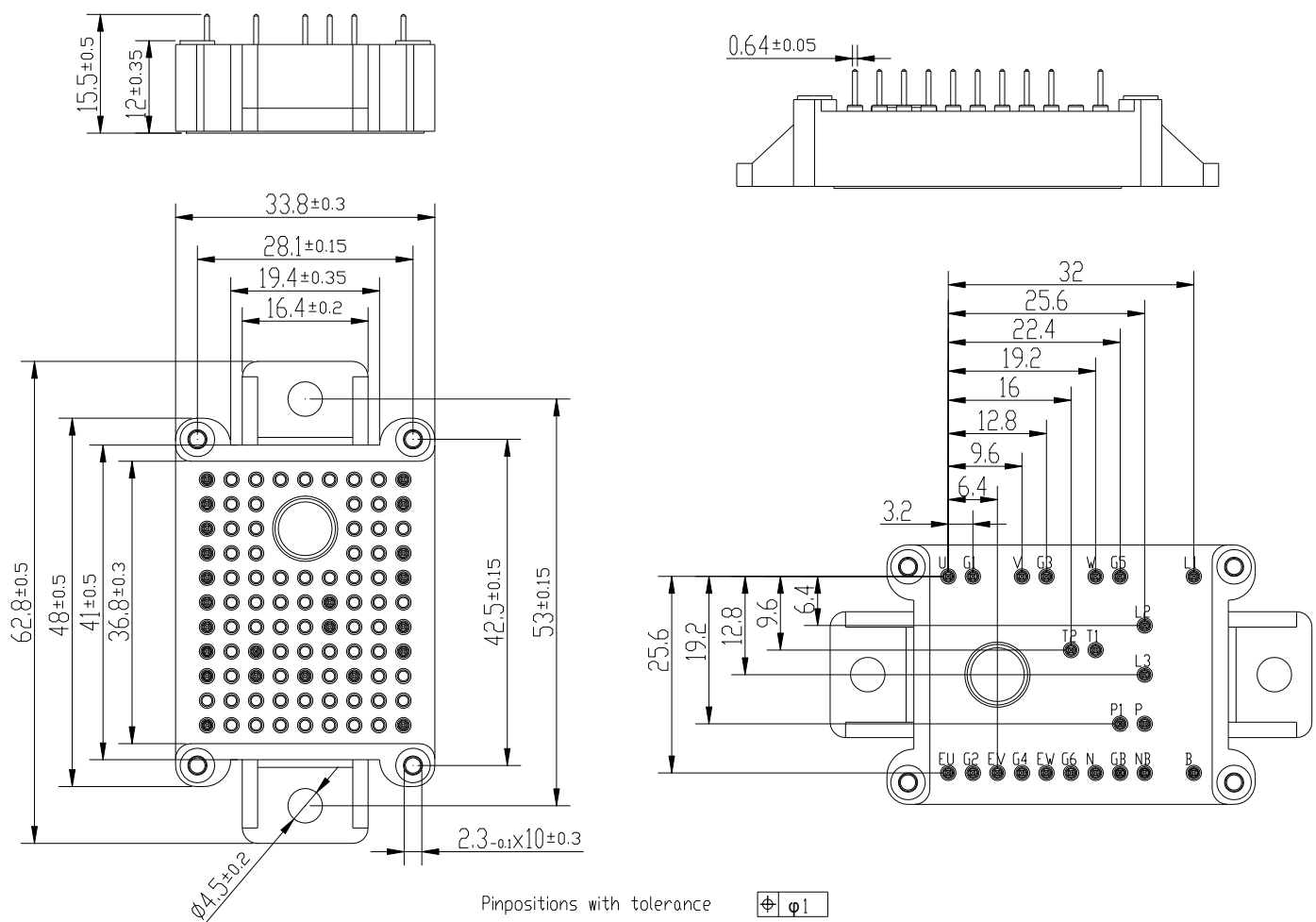
Fig 14. NTC Temperature Characteristic

## Circuit Schematic



## Package Dimensions

Dimensions in Millimeters



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